An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company



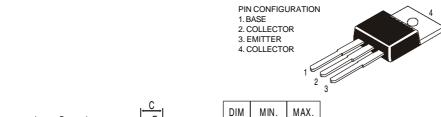


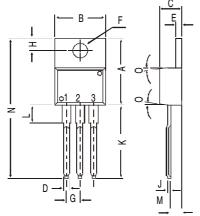
TO-220 Plastic Package

CSC2233

CSC2233 NPN PLASTIC POWER TRANSISTOR

TV Horizontal Deflection Output Applications





DIM	MIN.	MAX.	
Α	14.42	16.51	
В	9.63	10.67	
С	3.56	4.83	
D		0.90	
Е	1.15	1.40	
F	3.75	3.88	
G	2.29	2.79	
Н	2.54	3.43	
J		0.56	
K	12.70	14.73	
L	2.80	4.07	
М	2.03	2.92	
N		31.24	
0	DEG 7		
	A B C D E F G H J K L	A 14.42 B 9.63 C 3.56 D E 1.15 F 3.75 G 2.29 H 2.54 J K 12.70 L 2.80 M 2.03 N	

 V_{EBO}

 I_C

 I_{CP}

max.

max.

max.

5.0 V

4 A 10 A

ABSOLUTE MAXIMUM RATINGS

Emitter-base voltage (open collector)

Collector current (Peak value)

Collector current

Collector-base voltage (open emitter)	V_{CBO}	max.	200 V
Collector-emitter voltage (open base)	V_{CEO}	max.	60 V
Collector current	I_C	max.	4 A
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	40 W
Junction temperature	T_{j}	max.	150 °C
Collector-emitter saturation voltage	,		
$I_C = 4 A$; $I_B = 0.4 A$	V_{CEsat}	max.	1.0 V
D.C. current gain			
$I_C = 1 A$; $V_{CE} = 5 V$	h_{FE}	min.	30
		max.	150
RATINGS (at T_A =25°C unless otherwise specified)			
Limiting values			
Collector-base voltage (open emitter)	V_{CBO}	max.	200 V
Collector-emitter voltage (open base)	V_{CEO}	max.	60 V

Base current Total power dissipation up to $T_A = 25^{\circ}\text{C}$ Total power dissipation up to $T_C = 25^{\circ}\text{C}$ Junction temperature Storage temperature	I_{B} P_{tot} P_{tot} T_{j} T_{stg}	max. max. max. max. –65 to	1.0 A 1.5 W 40 W 150 ℃ +150 ℃
CHARACTERISTICS			
$T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified			
Collector cutoff current			
$I_E = 0; V_{CB} = 170 V$	I_{CBO}	max.	10 μΑ
Emitter cut-off current			
$I_C = 0$; $V_{EB} = 5 V$	I_{EBO}	max.	$10 \mu A$
Breakdown voltages			
$I_C = 20 \ mA; I_B = 0$	V_{CEO}	min.	60 V
$I_C = 1 mA; I_E = 0$	V_{CBO}	min.	200 V
$I_E = 1 mA; I_C = 0$	V_{EBO}	min.	5.0 V
Saturation voltages			
$I_C = 4 A$; $I_B = 0.4 A$	V_{CEsat}	max.	1.0 V
	V_{BEsat}	max.	1.5 V
D.C. current gain			
$I_C = 1 A; V_{CE} = 5 V$	h_{FE}	min.	30
		max.	150
$I_C = 4 A; V_{CE} = 5 V$ Transition frequency	h_{FE}	min.	20
$I_C = 0.5 A; V_{CE} = 5 V$	f_T	typ.	8 MHz

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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